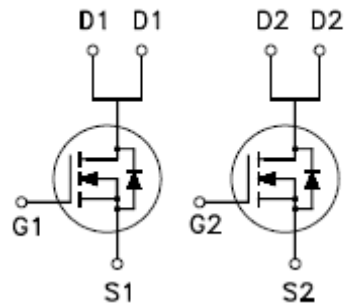
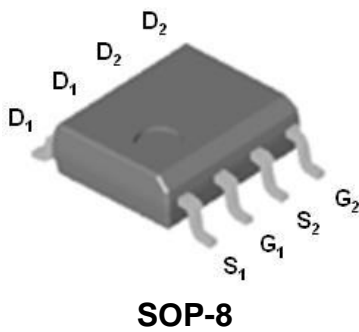


P2804HVG

Dual N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
40V	28m Ω @ $V_{GS} = 10V$	7A



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS	
Drain-Source Voltage	V_{DS}	40	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	I_D	$T_A = 25\text{ }^\circ\text{C}$	7	A
		$T_A = 70\text{ }^\circ\text{C}$	6	
Pulsed Drain Current ¹	I_{DM}	40		
Power Dissipation	P_D	$T_A = 25\text{ }^\circ\text{C}$	2	W
		$T_A = 70\text{ }^\circ\text{C}$	1.28	
Junction & Storage Temperature Range	T_j, T_{stg}	-55 to 150	$^\circ\text{C}$	
Lead Temperature ($1/16$ " from case for 10 sec.)	T_L	275		

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Lead	$R_{\theta JL}$		31	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		62.5	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

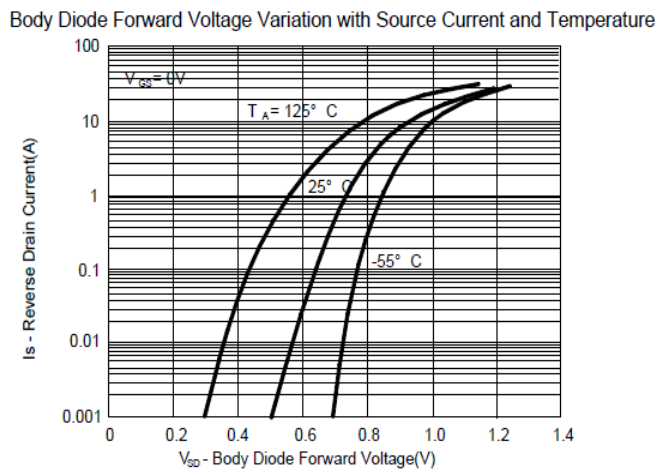
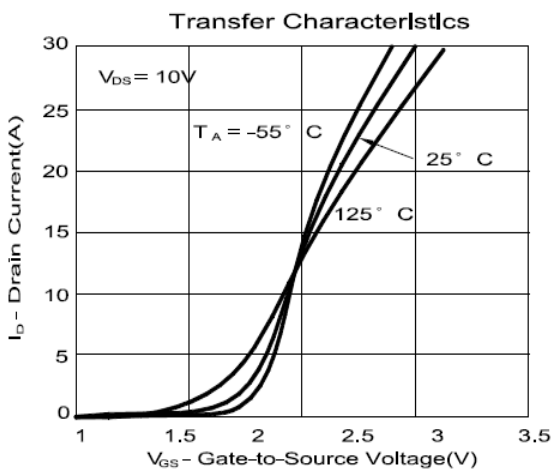
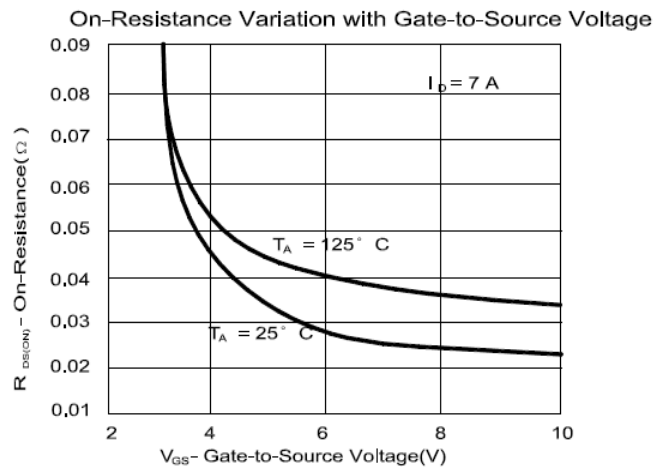
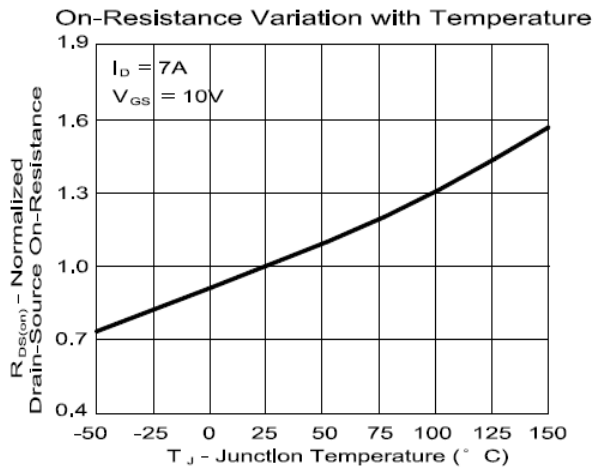
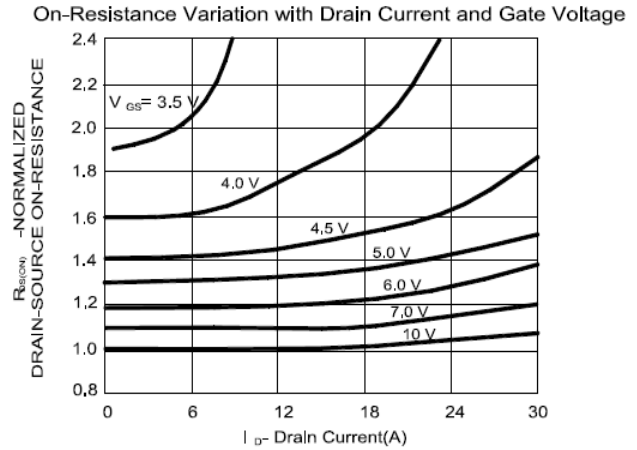
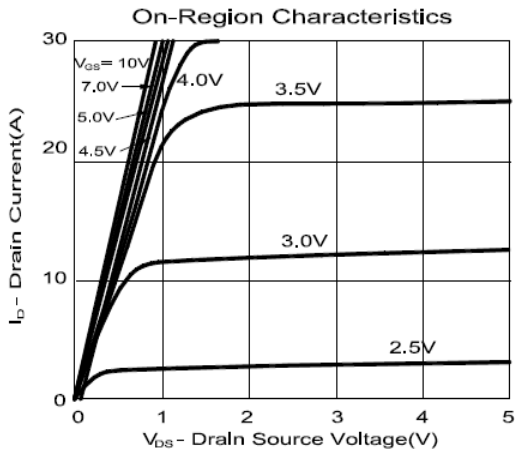
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	40			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	2	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 32V, V _{GS} = 0V			1	μA
		V _{DS} = 30V, V _{GS} = 0V, T _J = 55 °C			10	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 10V	20			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 7A		21	28	mΩ
		V _{GS} = 5V, I _D = 6A		27	42	
Forward Transconductance ¹	g _{fs}	V _{DS} = 10V, I _D = 5A		24		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 20V, f = 1MHz		742		pF
Output Capacitance	C _{oss}			103		
Reverse Transfer Capacitance	C _{riss}			94		
Total Gate Charge ²	Q _g	V _{DS} = 0.5V _{(BR)DSS} , V _{GS} = 10V, I _D = 7A		17.4		nC
Gate-Source Charge ²	Q _{gs}			4.1		
Gate-Drain Charge ²	Q _{gd}			4.4		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 20V, I _D ≅ 1A, V _{GS} = 10V, R _{GEN} = 6Ω		2.2		nS
Rise Time ²	t _r			7.5		
Turn-Off Delay Time ²	t _{d(off)}			11.8		
Fall Time ²	t _f			11		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS(T_J = 25 °C)						
Continuous Current	I _S				1.3	A
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			1	V
Reverse Recovery Time	t _{rr}	I _F = 5A, di _F /dt = 100A / μS		15.5		nS
Reverse Recovery Charge	Q _{rr}			7.9		nC

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

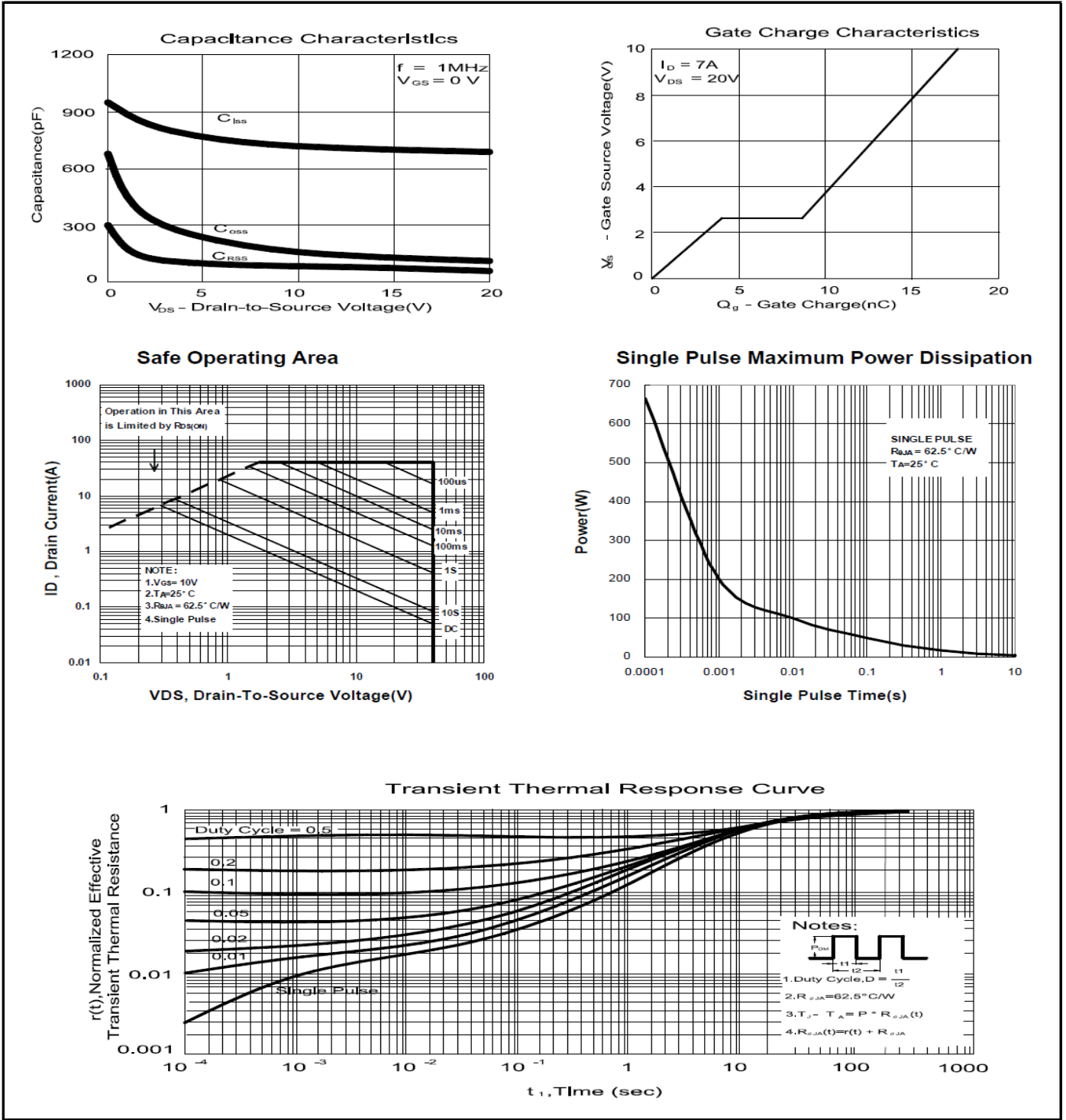
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Package Dimension

SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25				

